

# N-Channel Power MOSFET

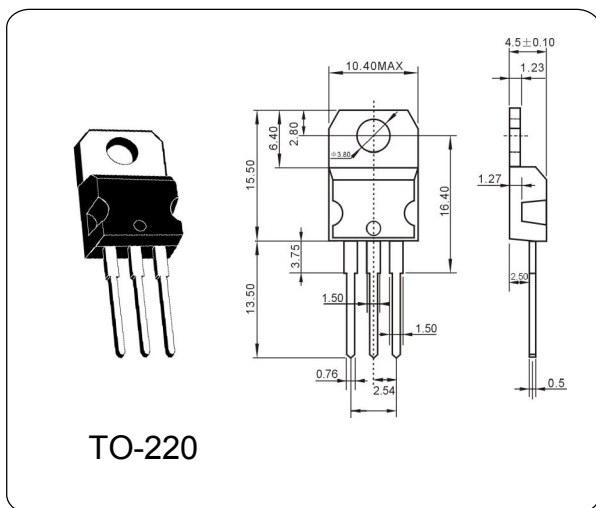
**IRFZ44N**

## DESCRIPTION

Process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

## ABSOLUTE MAXIMUM RATINGS ( Ta = 25 °C)

Parameter	I	Value	Unit
Drain-Source Voltage	$V_{DSS}$	55	V
Drain Current - Continuous	$I_D$	49	A
Drain Current - Pulsed	$I_{DM}$	160	A
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Power Dissipation	$P_D$	94	W
Max. Operating Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~150	°C



## ELECTRICAL CHARACTERISTICS ( Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250 \mu A$	55	—	—	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 55V, V_{GS} = 0V$	—	—	10	$\mu A$
Gate-Body Leakage Current, Forward	$I_{GSSF}$	$V_{GS} = 20V, V_{DS} = 0V$	—	—	100	nA
Gate-Body Leakage Current, Reverse	$I_{GSSR}$	$V_{GS} = -20V, V_{DS} = 0V$	—	—	-100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.0	3.0	4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 25A$	—	—	0.0175	$\Omega$
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 25A$	—	—	1.3	V